

November 1996



SEMICONDUCTOR TN

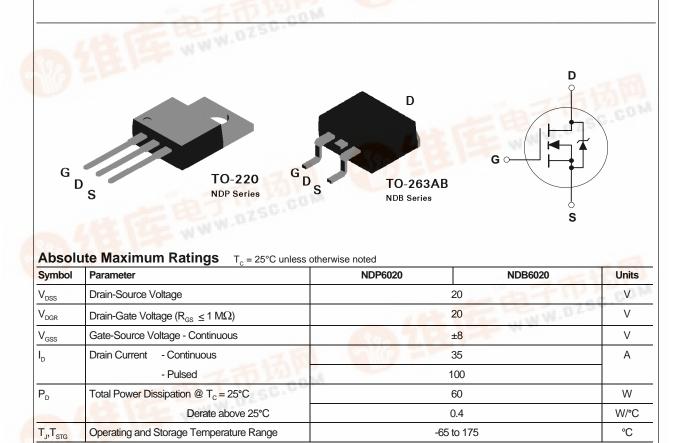
NDP6020 / NDB6020 N-Channel Logic Level Enhancement Mode Field Effect Transistor

General Description

These logic level N-Channel enhancement mode power field effect transistors are produced using National's proprietary, high cell density, DMOS technology. This very high density process has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as automotive, DC/DC converters, PWM motor controls, and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

Features

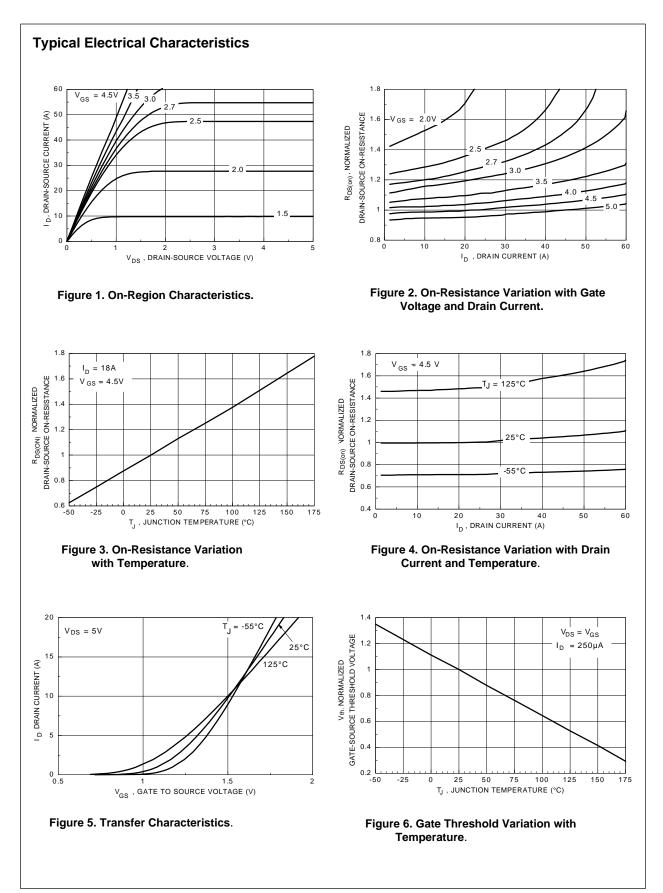
- $\begin{array}{c|c} \bullet & 35 \text{ A, } 20 \text{ V. } \text{R}_{\text{DS(ON)}} = 0.023 \ \Omega \ @ \ \text{V}_{\text{GS}} = 4.5 \text{ V} \\ \text{R}_{\text{DS(ON)}} = 0.028 \ \Omega \ @ \ \text{V}_{\text{GS}} = 2.7 \text{ V.} \end{array}$
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- 175°C maximum junction temperature rating.
- High density cell design for extremely low R_{DS(ON)}.
- TO-220 and TO-263 (D²PAK) package for both through hole and surface mount applications.

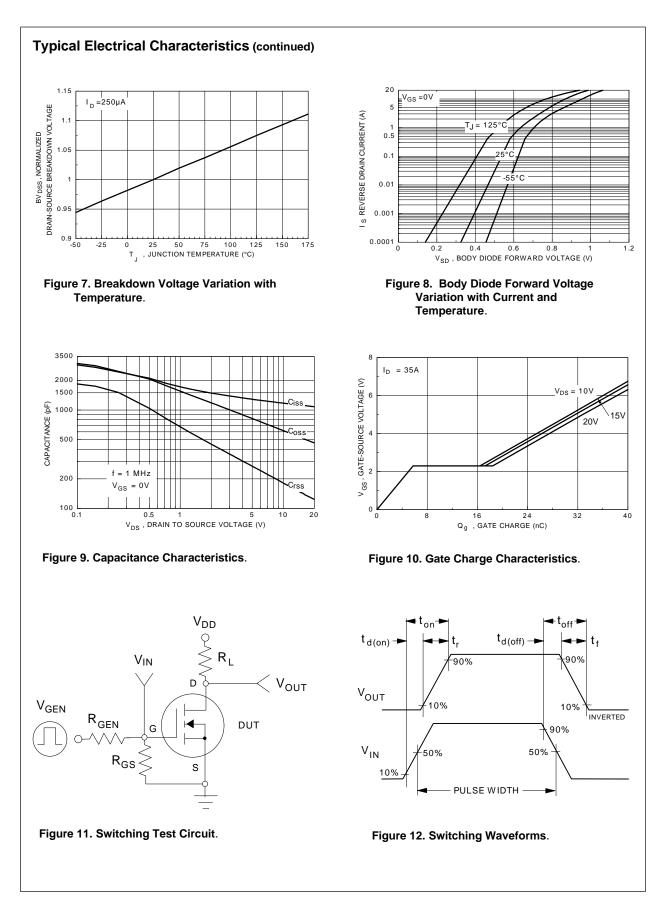


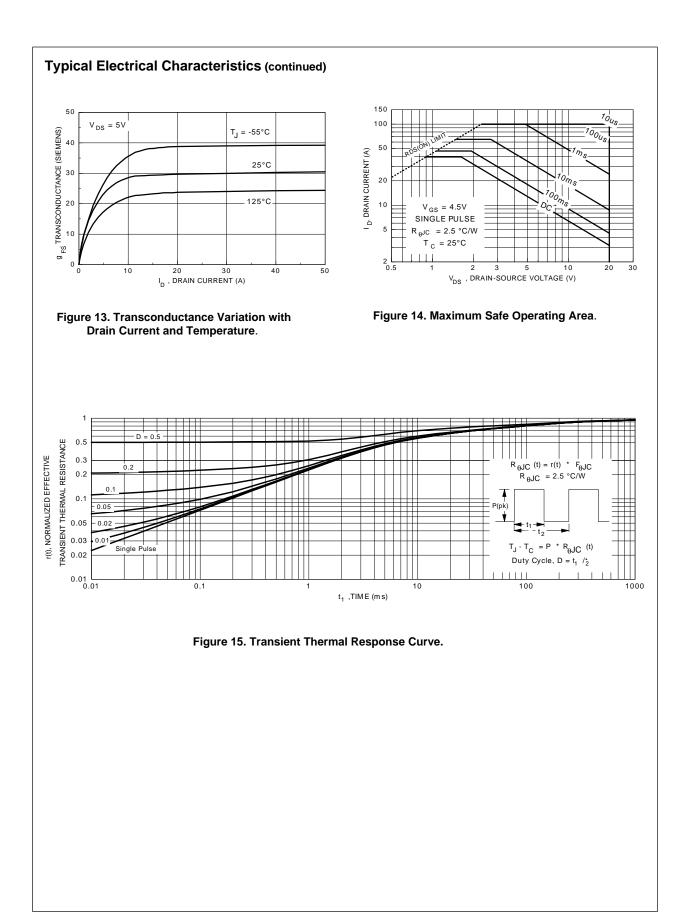
Symbol	Parameter	Conditions		Min	Тур	Max	Units
OFF CH	ARACTERISTICS	•					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_{D} = 250 \mu A$		20			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 16 V, V_{GS} = 0 V$				1	μA
			T _J = 55°C			10	mA
I _{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 8 V, V_{DS} = 0 V$				100	nA
	Gate - Body Leakage, Reverse	$V_{GS} = -8 V, V_{DS} = 0 V$				-100	nA
ON CHAI	RACTERISTICS (Note 1)						
V _{GS(th)}	Gate Threshold Voltage	$V_{\rm DS} = V_{\rm GS}, \ I_{\rm D} = 250 \ \mu A$		0.4	0.62	1	V
(-)			T _J = 125°C	0.2	0.35	0.7	
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 18 \text{ A}$			0.019	0.023	Ω
()			T _J = 125°C		0.024	0.032	İ
		$V_{GS} = 2.7 \text{ V}, I_{D} = 16 \text{ A}$			0.024	0.028	İ
I _{D(on)}	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$		60			Α
9 _{FS}	Forward Transconductance	$V_{\rm DS} = 5 \text{ V}, \text{ I}_{\rm D} = 18 \text{ A}$			29		S
DYNAMI	C CHARACTERISTICS	•					
C _{iss}	Input Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz			1170		pF
C _{oss}	Output Capacitance	f = 1.0 MHz			610		pF
C _{rss}	Reverse Transfer Capacitance				180		pF
	NG CHARACTERISTICS (Note 1)			1		1	<u> </u>
t _{D(on)}	Turn - On Delay Time	$V_{DD} = 20 \text{ V}, \text{ I}_{D} = 35 \text{ A},$ $V_{GS} = 5 \text{ V}, \text{ R}_{GEN} = 10 \Omega$ $\text{R}_{L} = 0.5 \Omega$			7	20	nS
t _r	Turn - On Rise Time				148	300	nS
t _{D(off)}	Turn - Off Delay Time				98	200	nS
t _f	Turn - Off Fall Time				233	450	nS
Q _g	Total Gate Charge	V _{DS} = 15 V,			32	45	nC
Q _{gs}	Gate-Source Charge	$I_{\rm D} = 35 \text{A}, V_{\rm GS} = 5 \text{V}$			6		nC
Q _{gd}	Gate-Drain Charge	_			11		nC

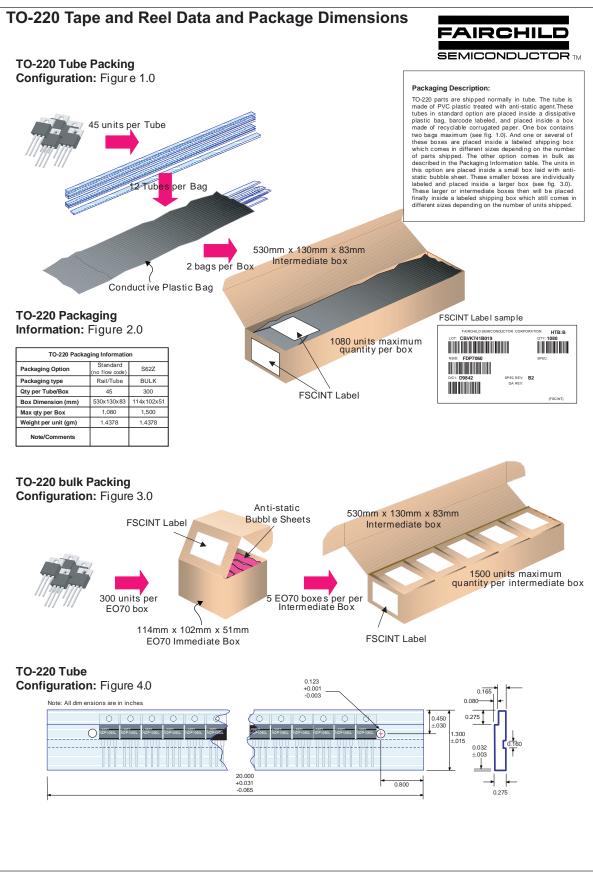
Electrical Characteristics (T _c = 25°C unless otherwise noted)						
Symbol	Parameter	Conditions	Min	Тур	Max	Units
DRAIN-SO	OURCE DIODE CHARACTERISTICS					
I _s	Maximum Continuous Drain-Source Diode Forward Current				35	А
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				100	А
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{S} = 35 \text{ A} \text{ (Note 1)}$		1.1	1.3	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_F = 35 \text{ A}, \\ -dI_F/dt = 100 \text{ A}/\mu\text{s}$		43	90	ns
l _{rr}	Reverse Recovery Current			1.1	3	A
THERMA	L CHARACTERISTICS					
R _{_θJC}	Thermal Resistance, Junction-to-Case				2.5	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient				62.5	°C/W

Note: 1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

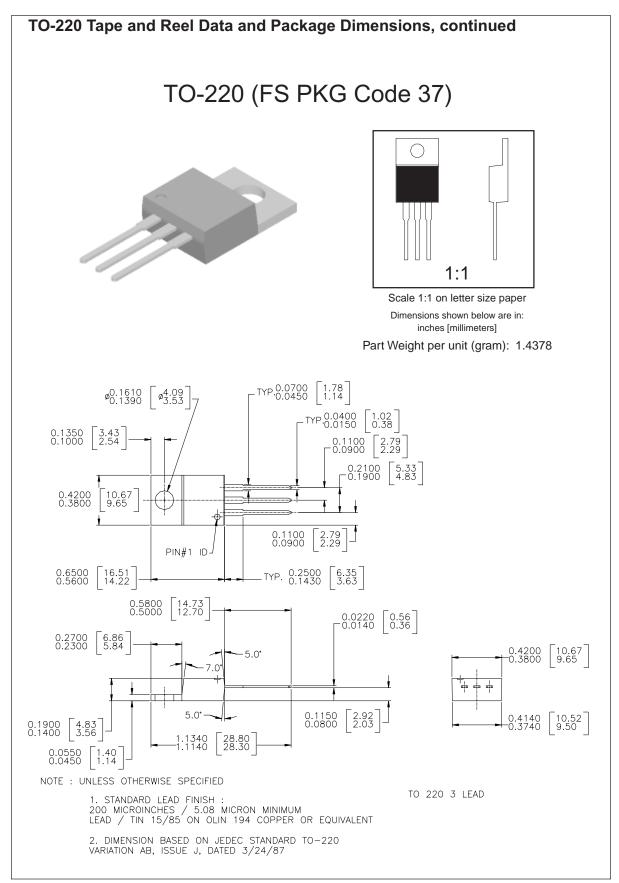


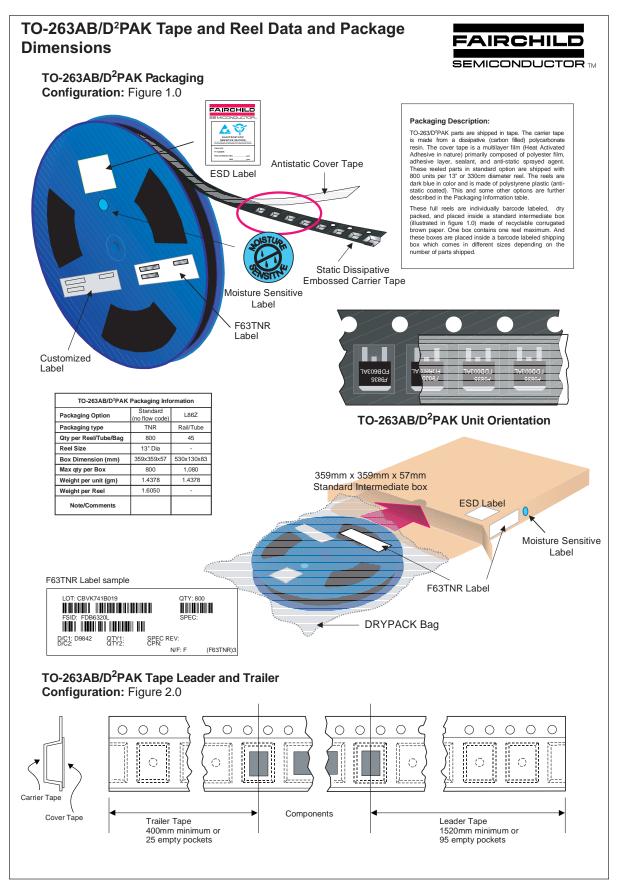


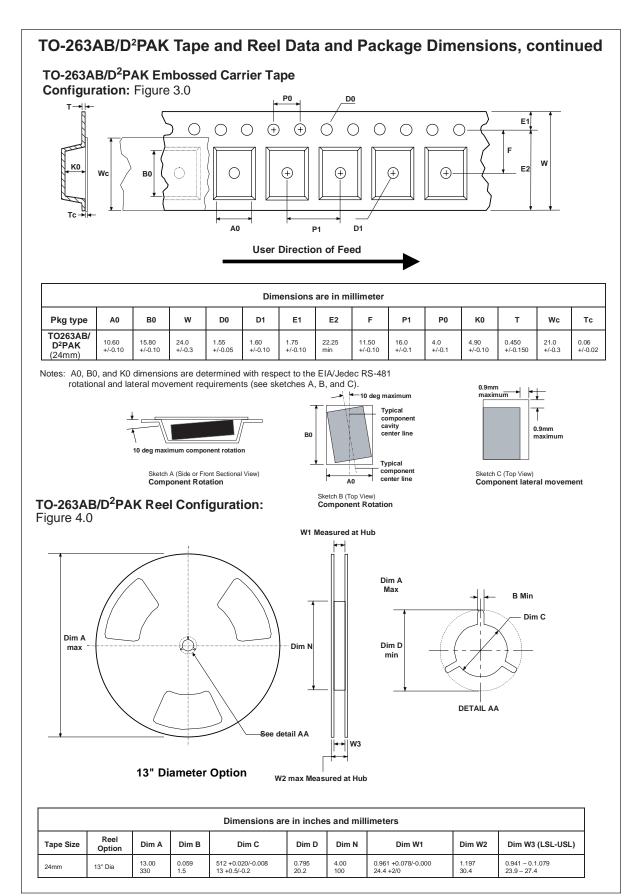


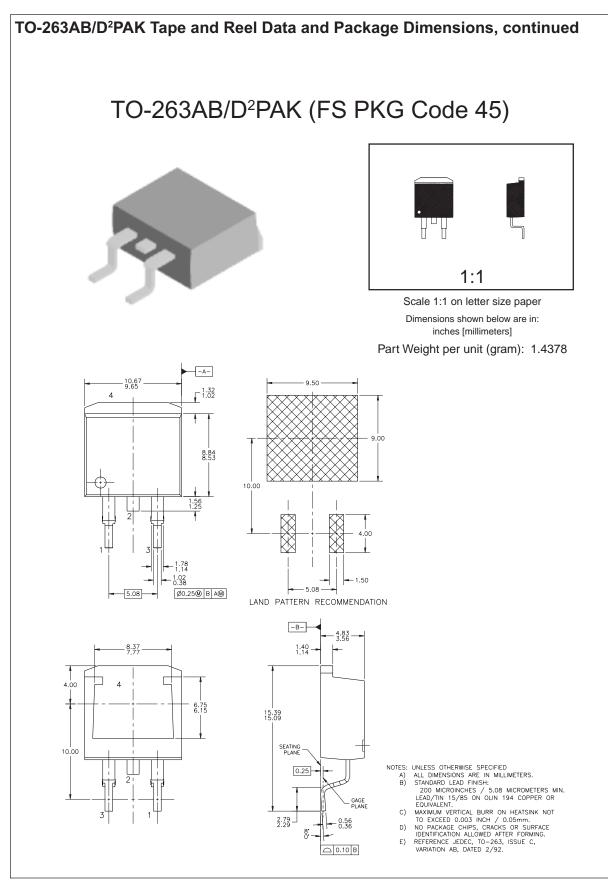


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